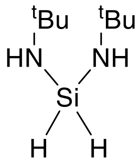
Catalog # 14-1060 Bis(t-butylamino)silane, 97+% BTBAS



Thermal Behavior:

- Boiling point: 167°C
- Vapor Pressure: ~1.87 Torr/25°C, 6.5 torr/40-45°C [1-2]; Diagram is available in [1]

Technical Notes:

1. ALD low temperature precursor for the silicon oxide and silicon nitride thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SiO_2	ALD Therm. Pl.	50°C	-	O_3, PlO_2	250-350°C 50-200°C	3-5
SiN_x	ALD	50°C	-	PlN_2	100-500°C,	6-8

References:

1. *Solid State Technol.*, **2000**, *43,* 79.
2. *J. Electrochem. Soc.*, **2005**, *152,* G316.
3. *Thin Solid Films,* **2014**, *558,* 93.
4. *J. Phys. Chem. C,* **2016**, *120,* 10927.
5. *ACS Appl. Mater. Interfaces* **2017**, *9,* 42928.
6. *Appl. Phys. Lett.* **2015**, *107,* 014102.
7. *Chem. Mater.* **2016**, *28,* 5864.
8. *ACS Appl. Mater. Interfaces,* **2017**, *9,* 1858.